

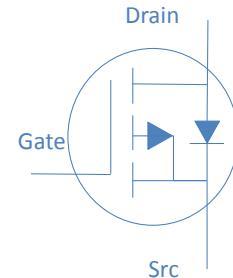
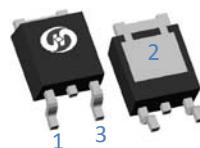
**30V P-Ch Power MOSFET**
**Feature**

- ◇ High Speed Power Switching, Logic Level
- ◇ Enhanced Avalanche Ruggedness
- ◇ 100% UIS Tested, 100% Rg Tested
- ◇ Lead Free, Halogen Free

$V_{DS}$	-30	V
$R_{DS(on),typ}$	$V_{GS}=10V$	17 mΩ
$R_{DS(on),typ}$	$V_{GS}=4.5V$	25 mΩ
$I_D$ (Silicon Limited)	-35	A

**Application**

- ◇ Hard Switching and High Speed Circuit
- ◇ DC/DC in Telecoms and Industrial

**TO-252**


Part Number	Package	Marking
HTD200P03	TO-252	TD200P03

**Absolute Maximum Ratings at  $T_j=25^\circ C$  (unless otherwise specified)**

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	$I_D$	$T_C=25^\circ C$	-35	A
		$T_C=100^\circ C$	-26	
Drain to Source Voltage	$V_{DS}$	-	-30	V
Gate to Source Voltage	$V_{GS}$	-	$\pm 25$	V
Pulsed Drain Current	$I_{DM}$	-	-70	A
Avalanche Energy, Single Pulse	$E_{AS}$	$L=0.1mH, T_C=25^\circ C$	5	mJ
Power Dissipation	$P_D$	$T_A=25^\circ C$	42	W
Operating and Storage Temperature	$T_J, T_{stg}$	-	-55 to 150	°C

**Absolute Maximum Ratings**

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance Junction-Case	$R_{\theta JC}$	3	°C/W

**Electrical Characteristics at  $T_j=25^\circ\text{C}$  (unless otherwise specified)**
**Static Characteristics**

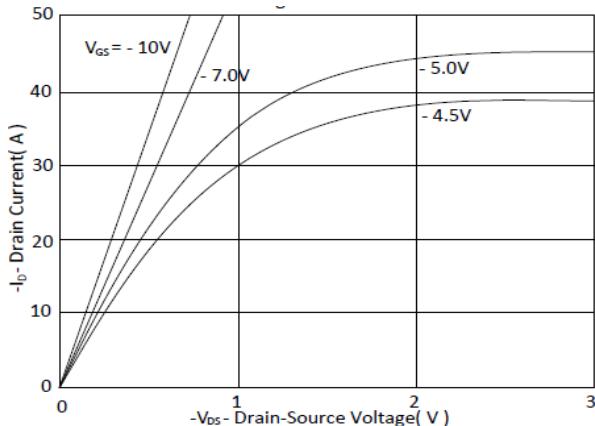
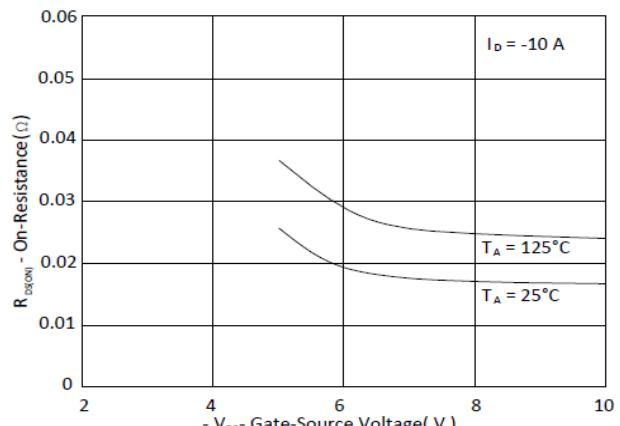
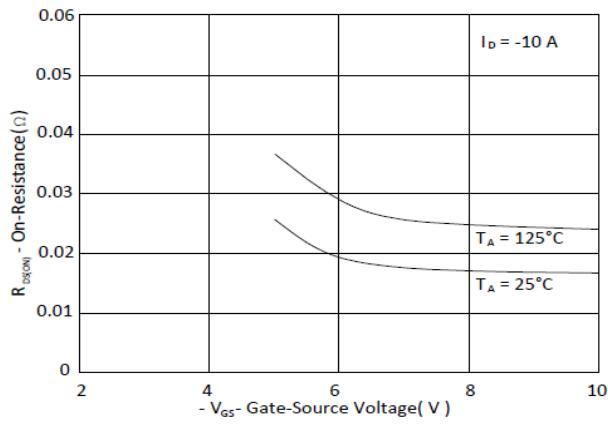
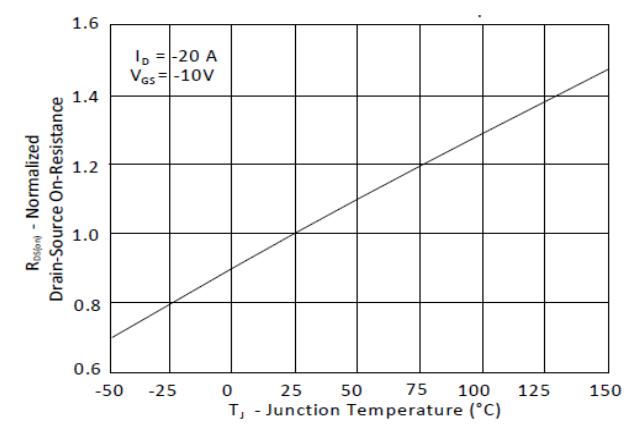
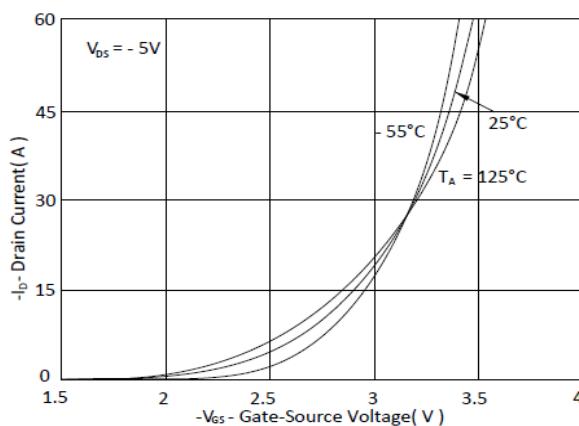
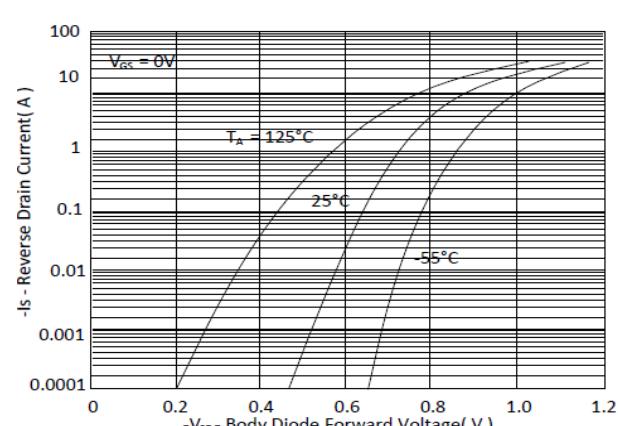
Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_D=-250\mu\text{A}$	-30	-	-	V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}, I_D=-250\mu\text{A}$	-1.0	-1.5	-3.0	
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=-24\text{V}, T_j=25^\circ\text{C}$	-	-	-1	$\mu\text{A}$
		$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=-20\text{V}, T_j=125^\circ\text{C}$	-	-	-10	
Gate to Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm100$	nA
		$V_{\text{GS}}=\pm25\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm500$	nA
Drain to Source on Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=-10\text{V}, I_D=-20\text{A}$	-	17	20	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_D=-10\text{A}$	-	25	34	
Transconductance	$g_{\text{fs}}$	$V_{\text{DS}}=-5\text{V}, I_D=-20\text{A}$	-	24	-	S
Gate Resistance	$R_G$	$V_{\text{GS}}=15\text{mV}, V_{\text{DS}}=0\text{V}, f=1\text{MHz}$	-	4.5	-	$\Omega$

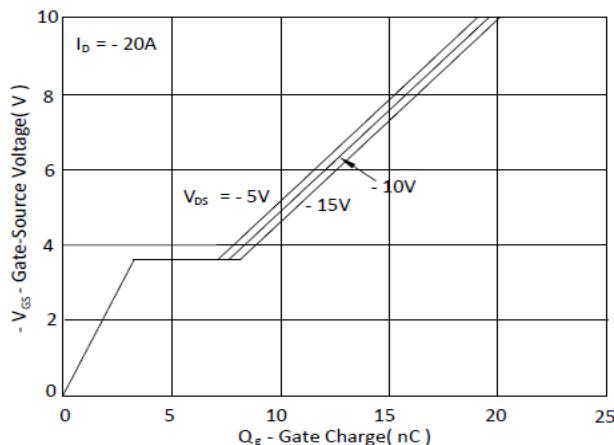
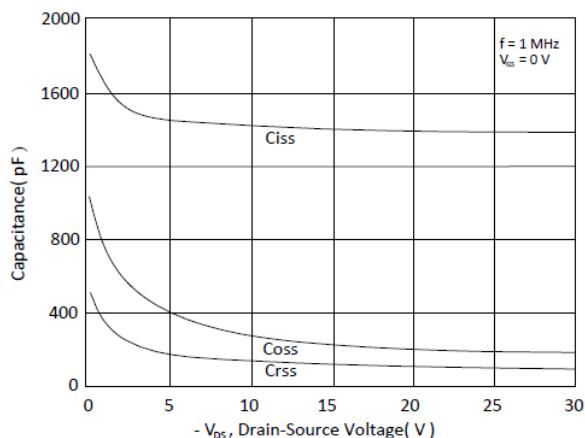
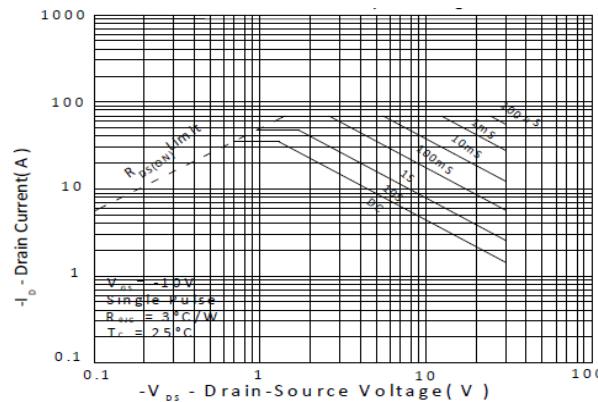
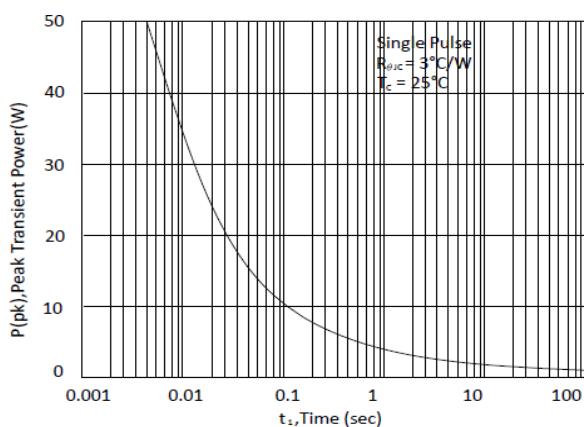
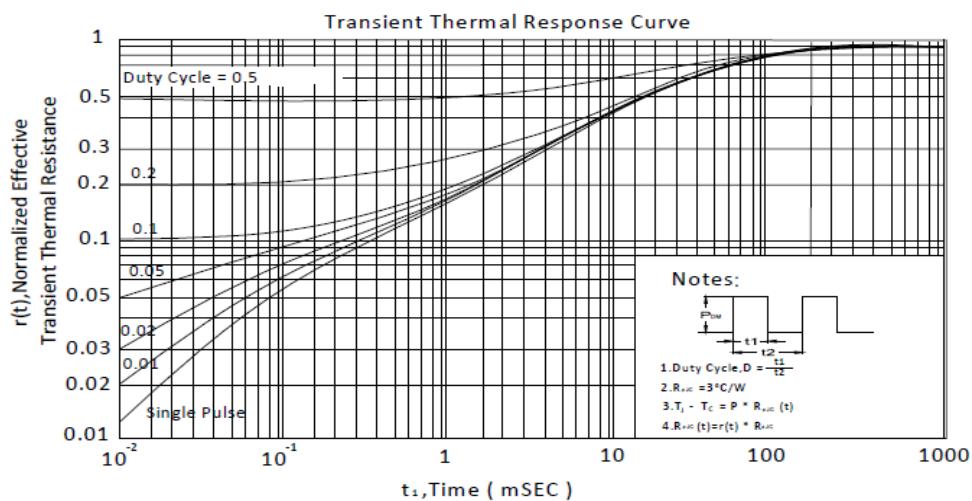
**Dynamic Characteristics**

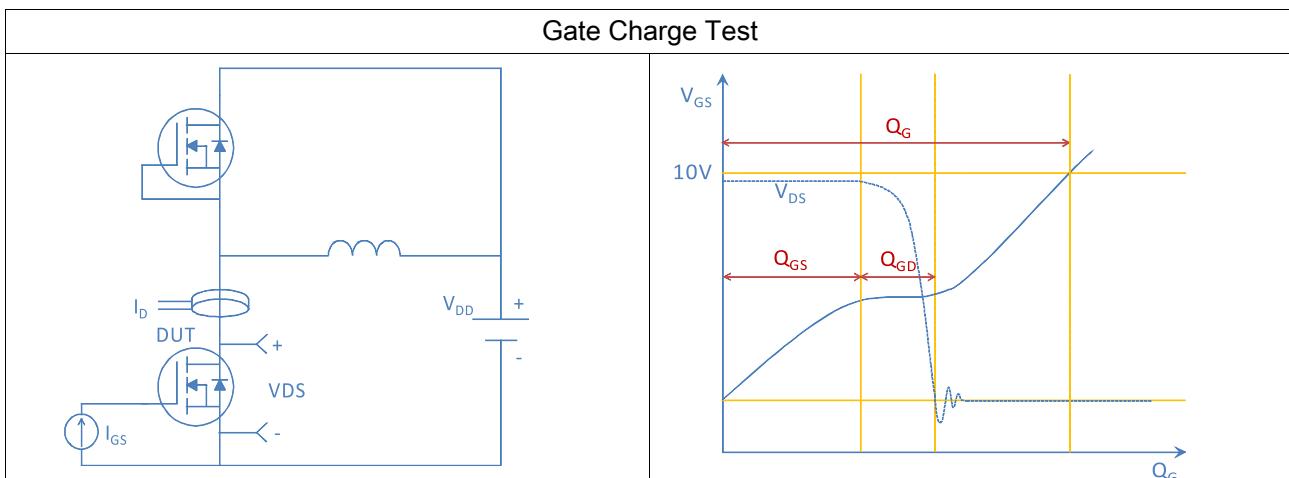
Input Capacitance	$C_{\text{iss}}$	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=-15\text{V}, f=1\text{MHz}$	-	1407	-	pF
Output Capacitance	$C_{\text{oss}}$		-	208	-	
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	164	-	
Total Gate Charge	$Q_g(10\text{V})$	$V_{\text{DD}}=-15\text{V}, I_D=-20\text{A}, V_{\text{GS}}=-10\text{V}$	-	20.3	-	nC
	$Q_g(4.5\text{V})$		-	9.8	-	
Gate to Source Charge	$Q_{\text{gs}}$		-	3.2	-	
Gate to Drain (Miller) Charge	$Q_{\text{gd}}$		-	4.9	-	
Turn on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=-15\text{V}, I_D=-1\text{A}, V_{\text{GS}}=-10\text{V}, R_G=2.7\Omega$	-	10	-	ns
Rise time	$t_r$		-	8	-	
Turn off Delay Time	$t_{\text{d}(\text{off})}$		-	25	-	
Fall Time	$t_f$		-	6	-	

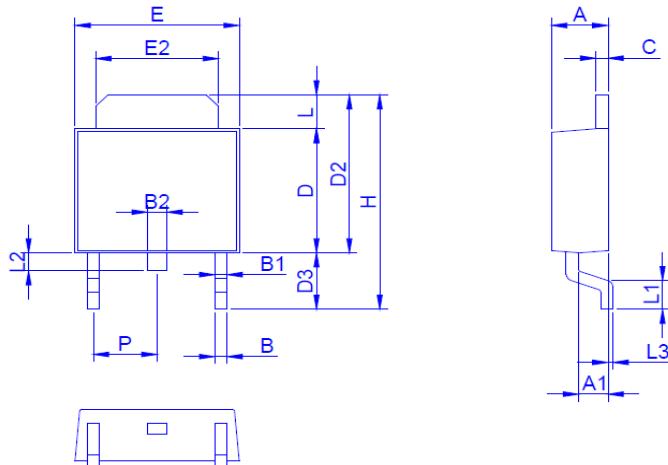
**Reverse Diode Characteristics**

Diode Forward Voltage	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_F=-20\text{A}$	-		-1.3	V
Reverse Recovery Time	$t_{\text{rr}}$	$I_F=-35\text{A}, dI_F/dt=100\text{A}/\mu\text{s}$	-	32	-	ns
Reverse Recovery Charge	$Q_{\text{rr}}$		-	26	-	nC

**Fig 1. Typical Output Characteristics**

**Figure 2. On-Resistance vs. Gate-Source Voltage**

**Figure 3. On-Resistance vs. Drain Current and Gate Voltage**

**Figure 4. Normalized On-Resistance vs. Junction Temperature**

**Figure 5. Typical Transfer Characteristics**

**Figure 6. Typical Source-Drain Diode Forward Voltage**


**Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage**

**Figure 8. Typical Capacitance vs. Drain-to-Source Voltage**

**Figure 9. Maximum Safe Operating Area**

**Figure 10. Single Pulse Maximum Power Dissipation**

**Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient**




**Package Outline**
**TO-252, 3leads**


Dimension	A	A1	B	B1	B2	C	D	D2	D3	E	E2	H	L	L1	L2	L3	P
Min.	2.10	0.95	0.30	0.40	0.60	0.40	5.30	6.70	2.20	6.40	4.80	9.20	0.89	0.90	0.50	0.00	2.10
Max.	2.50	1.30	0.85	0.94	1.00	0.60	6.20	7.30	3.00	6.70	5.45	10.15	1.70	1.65	1.10	0.30	2.50